LED Lighting

Solution Proposal by Toshiba













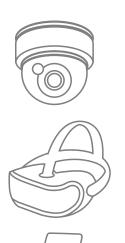








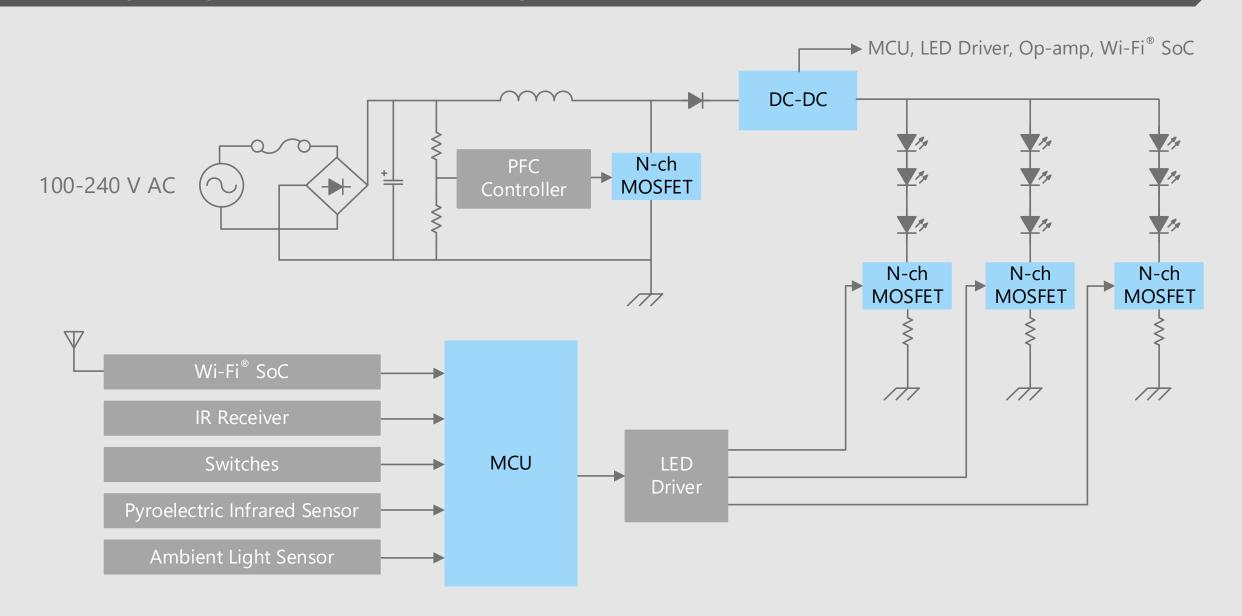
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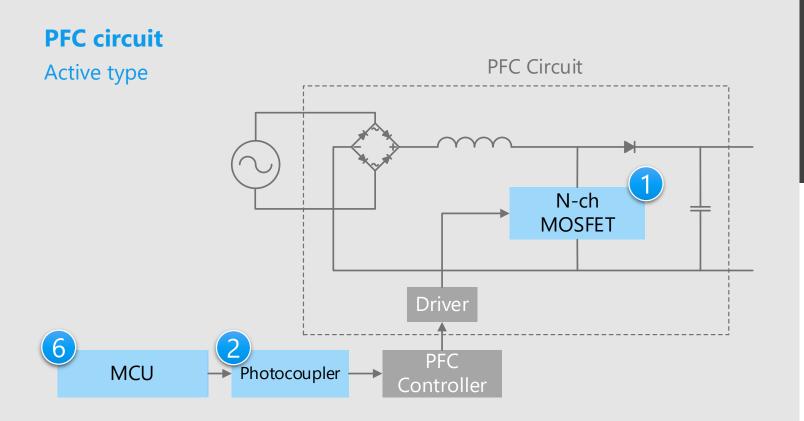
Block Diagram

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LED lighting Overall block diagram



LED lighting Detail of power supply unit (1)



* Click on the number in the circuit diagram to jump to the detailed description page

Criteria for device selection

- MOSFET is suitable for active type PFC circuit.
- The transistor coupler is for signal isolation.
- MCU can be used for PFC control.

Proposals from Toshiba

- Suitable for high efficiency power supply switching
 - DTMOSVI Series MOSFET
- High current transfer ratio and high
 temperature operation makes easy to design
 Transistor output photocoupler
- Built-in analog input interface at low power consumption and efficient software development

MCU M380 Group



LED lighting Detail of power supply unit (2)

DC-DC converter circuits Flyback type N-ch **MOSFET** N-ch **MOSFET** Driver Detection & Control Comparison Photocoupler <</p> Circuit Forward type N-ch **MOSFET MOSFET** N-ch **MOSFET** Driver Detection & Control Comparison Photocoupler -Circuit

* Click on the number in the circuit diagram to jump to the detailed description page

Criteria for device selection

- By using a MOSFET with low on-resistance and high heat dissipation efficiency, a set having low heat generation and low power consumption is realized.
- The transistor coupler is for signal isolation.
- Small package products contribute to the reduction of circuit board area.

Proposals from Toshiba

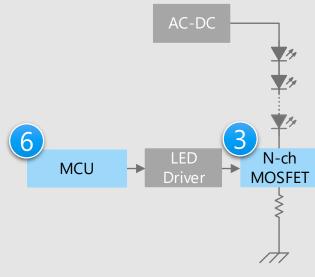
- Suitable for high efficiency power supply switching
 - DTMOSVI Series MOSFET
- **High current transfer ratio and high** temperature operation makes easy to design Transistor output photocoupler
- **MOSFET** with low on-resistance and high heat dissipation efficiency

U-MOS Series MOSFET



LED lighting Detail of LED drive unit

LED drive circuit



* Click on the number in the circuit diagram to jump to the detailed description page

Criteria for device selection

 By using a MOSFET with low on-resistance and high heat dissipation efficiency, a set having low heat generation and low power consumption is realized.

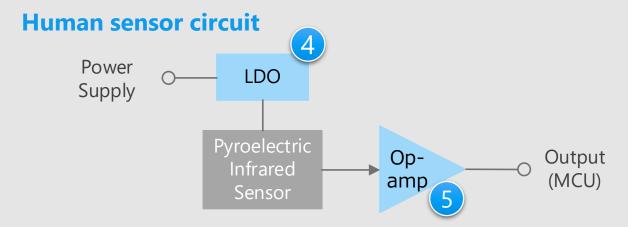
Proposals from Toshiba

- MOSFET with low on-resistance and high heat dissipation efficiency
 - **U-MOS Series MOSFET**
- Built-in analog input interface at low power consumption and efficient software development

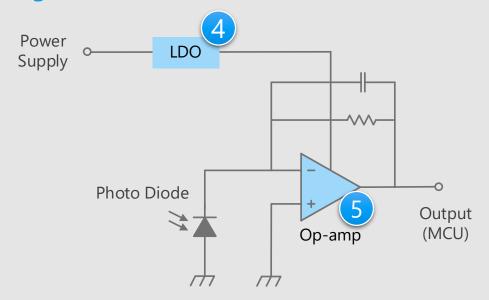
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LED lighting Detail of sensor signal input unit



Ambient light sensor circuit



* Click on the blue circled numbers above to view detailed descriptions.

Criteria for device selection

- PSRR (Power Supply Rejection Ratio) of LDO regulator is an important parameter for sensor modules.
- The operational amplifier should be low current consumption or low noise device.

Proposals from Toshiba

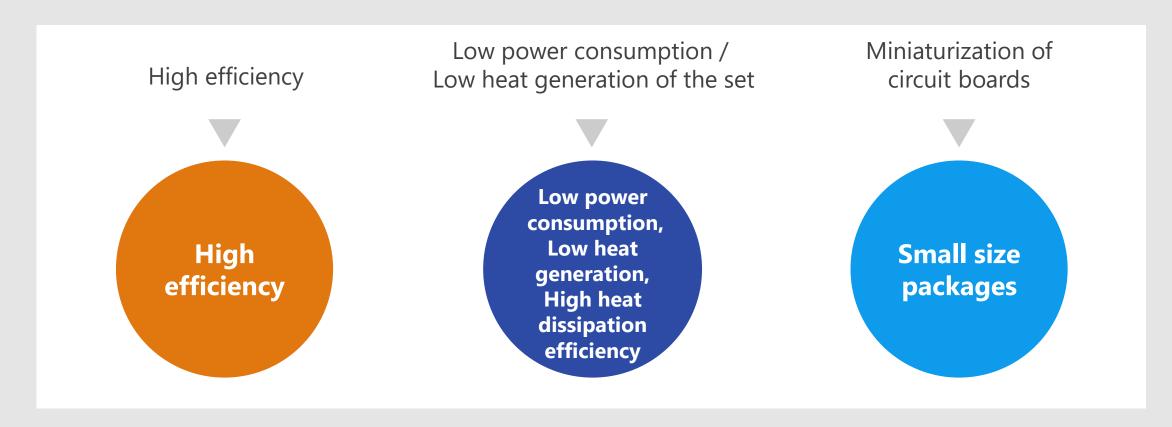
- Supply the power with low noise
 Small surface mount LDO regulator
- Amplification of detected very small signal with low noise
 - Low current consumption op-amp
 / Low noise op-amp



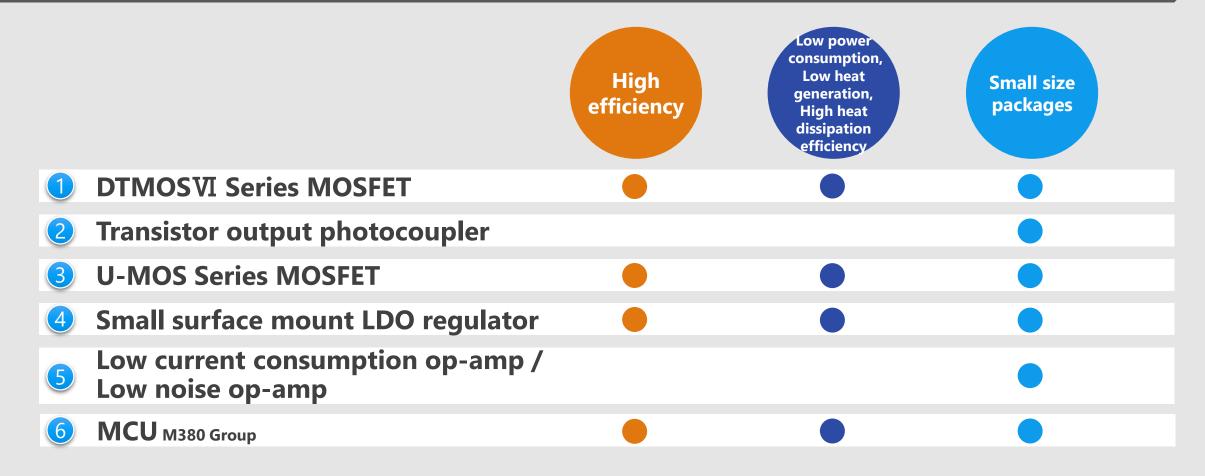


Device solutions to address customer needs

As described above, in the design of LED lighting, "High efficiency", "Low power consumption / Low heat generation of set" and "Miniaturization of circuit boards" are important factors. Toshiba's proposals are based on these three solution perspectives.



Device solutions to address customer needs





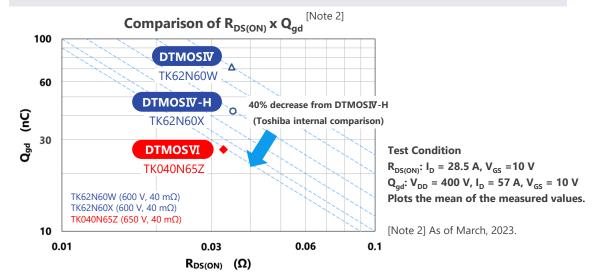




Realizes improvement of power supply efficiency by 40 % (comparison of Toshiba's conventional products) reduction of $R_{DS(ON)} \times Q_{gd}$.

 $R_{DS(ON)}$ x Q_{gd} reduced by 40 %

Using a single epitaxial process, the figure of merit $R_{DS(ON)} \times Q_{gd}$ was reduced by 40 % by optimizing the structure (comparison of Toshiba's DTMOSIV-H 600 V products). By realizing low $R_{DS(ON)} \times Q_{gd}$, device switching loss was reduced contributing to improvement in power supply efficiency of equipment.



2 RonA reduced by 18 %

The figure of merit RonA of the latest generation [Note1] DTMOSVI has been reduced by 18 % compared with the previous generation (Toshiba's DTMOSVI 650 V products). Achieving low on-resistance while maintaining high voltage contributes to high efficiency of equipment.

[Note1] As of March, 2023

Lineup							
Part number		TK065U65Z	TK040N65Z				
Package		TOLL	TO-247				
V _{DSS} [V]	V _{DSS} [V]		650				
I _D [A]	I _D [A]		57				
$R_{DS(ON)}[\Omega]$	Тур.	0.051	0.033				
$R_{DS(ON)} [\Omega]$ $@V_{GS} = 10 \text{ V}$	Max	0.065	0.04				
Polarity		N-ch	N-ch				

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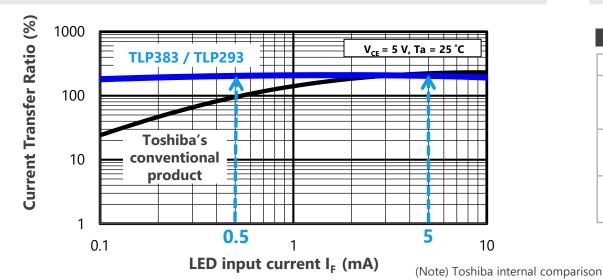




High CTR (Current Transfer Ratio) is realized even in low input current range ($I_F = 0.5 \text{ mA}$).

High current transfer ratio

The TLP383 and TLP293 are high isolation photocouplers that optically couple a phototransistor and high output infrared LED. Compared to Toshiba's conventional products (TLP385), higher CTR (Current Transfer Ratio) in low input current range ($@I_F = 0.5$ mA) is realized.



Designed for high temperature operation

The TLP383 and TLP293 are designed to operate even under severe ambient temperature conditions.

Lineup								
Part number	TLP383	TLP293	TLP385					
Package	4pin SO6L	SO4	4pin SO6L					
BV _s [Vrms]	5000	3750	5000					
T _{opr} [°C]	-55 to 125	-55 to 125	-55 to 110					

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Contributes to lower heat generation of system by providing low on-resistance lineup and a highly heat dissipation package (DSOP Advance).

Low R_{DS(ON)} (on-resistance)

By keeping the $R_{DS(ON)}$ (drain-source on-resistance) low, heat build-up and power consumption can be reduced. Products are prepared from on-resistance of 0.36 m Ω (Typ.).

Small Qoss

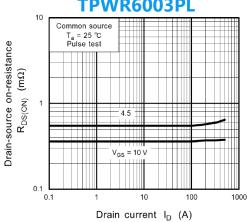
Contributes low loss due to small Q_{OSS} . TPWR8004PL's performance index $R_{DS(ON)}$ x Q_{OSS} is deducted to 5 % ^[Note] than competitor's products.

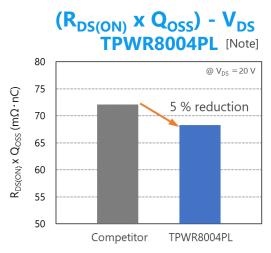
3 Variety of packages

Adding SOP Advance of industry standard package, DSOP Advance of double-side heat dissipation package on same footprint had been prepared. Packages can be selected according to the set.

[Note] Comparison with competitor's product with equivalent ratings. As of March, 2023. Based on Toshiba's measurement data.







Lineup							
Part numbe	er	TPWR6003PL	TPWR8004PL	TPHR7404PU	TPHR8504PL		
Package		DSOP Advance		SOP Advance			
V _{DSS} [V]		30	40	40 40			
I _D [A]		150 (412*)	150 (340*)	150 (400*)	150 (340*)		
$R_{DS(ON)}$ [m Ω]	$R_{DS(ON)}[m\Omega]$ Typ.	0.36	0.65	0.51	0.7		
$@V_{GS} = 10 \text{ V}$ Max		0.6	0.8	0.74	0.85		
Polarity		N-ch	N-ch	N-ch	N-ch		
Generation		U-MOSIX-H	U-MOSIX-H	U-MOSIX-H	U-MOSIX-H		

^{*:} Silicon limit

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Lineup of low on-resistance products is provided and trade-off between on-resistance and capacitance contribute to higher power supply efficiency.

Fast switching speed

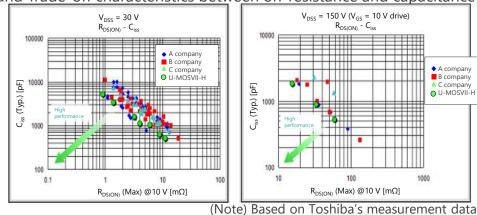
Reducing switching loss through high speed operation contributes to higher power supply efficiency. **Small gate input charge**

Small gate input charge reduces the performance required for driving the MOSFET. It contributes to improving switching characteristics.

3 Low on-resistance

By reducing the on-resistance between the drain and source, heat generation and power consumption can be kept low.

Lineup of low on-resistance products and Trade-off characteristics between on-resistance and capacitance



Lineup							
Part number	TPH2R408QM	TPH4R008QM	TPN8R408QM	TPN12008QM	TPN19008QM	TK5R1P08QM	TK6R9P08QM
Package	ackage SOP Advance(N)			SON Advance	DPAK		
V _{DSS} [V]	80	80	80	80	80	80	80
I _D [A]	120 (200*)	86 (140*)	32 (77*)	26 (60*)	34 (38*)	84 (105*)	62 (83*)
R _{DS(QNI)} [mΩ] Typ	o. 1.9	3.1	6.5	9.6	14.7	4.2	5.5
$R_{DS(ON)}$ [m Ω] Tyl @V _{GS} = 10 V Ma	2.43	4	8.4	12.3	19	5.1	6.9
Polarity	N-ch	N-ch	N-ch	N-ch	N-ch	N-ch	N-ch
Generation	U-MOSX-H	U-MOSX-H	U-MOSX-H	U-MOSX-H	U-MOSX-H	U-MOSX-H	U-MOSX-H

^{*:} Silicon limit

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Small surface mount LDO regulator TCR15AG / TCR13AG / TCR8BM / TCR5BM / TCR5RG / TCR3RM / TCR3U / TCR2L / TAR5 Series



consumption

Low heat
generation,
High heat
dissipation
efficiency



Value provided

Wide lineup from general purpose type to small package type are provided. Contribute to realize a stable power supply not affected by fluctuation of battery.

Low dropout voltage

The originally developed latest process significantly improved the dropout voltage characteristics.

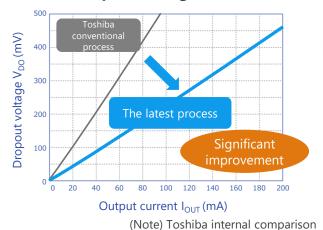
High PSRR Low output noise voltage

Many product series that realize both high PSRR (Power Supply Rejection Ratio) and low output noise voltage characteristics are provided. They are suitable for stable power supply for analog circuit.

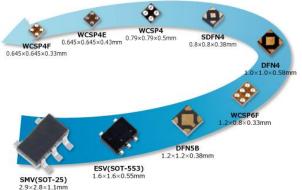
3 Low current consumption

 $0.34~\mu A$ of $I_{B(ON)}$ is realized by utilizing CMOS process and unique circuit technology. (TCR3U Series)

Low dropout voltage



Rich package lineup



Lineup									
Part number	TCR15AG Series	TCR13AG Series	TCR8BM Series	TCR5BM Series	TCR5RG Series	TCR3RM Series	TCR3U Series	TCR2L Series	TAR5 Series
Features		Low dropout voltage Low noise High PSRR Low current consumption		noise urrent	Low current consumption		15 V Input voltage Bipolar type		
I _{OUT} (Max) [A]	1.5	1.5 1.3 0.8 0.		0.3		.3	0.2		
PSRR (Typ.) [dB] @f = 1 kHz	95	90	98	98	100	100	70	-	70
I _B (Typ.) [μΑ]	25	56	20	19	7	7	0.34	1	170

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Low current consumption op-amp / Low noise op-amp tc755102F / Tc75567TU







Value provided

Low current consumption type and low noise type operational amplifiers maximize the performance of system.

Low voltage operation

We have a lineup of low power supply voltage-driven operational amplifiers using CMOS process for low power supply voltage-driven wearable equipment.

Low current consumption (TC75S102F) $I_{DD} = 0.27 \, [\mu A] \, (Typ.)$

CMOS processes have been used to achieve lower current consumption. This contributes to lower power consumption and longer life of wearable equipment.

SolutionLow noise (TC75S67TU)

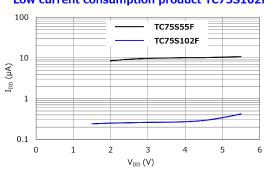
V_{NI} = 6.0 [nV/√Hz] (Typ.) @f = 1 kHz

This CMOS operational amplifier can amplify minute signals detected by various sensors [Note] with very low noises. By optimizing the process, the equivalent input noise voltage has been reduced.

TC75S102F

Current Consumption Characteristic (Toshiba internal comparison)

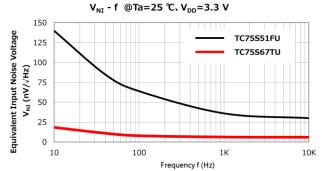
Low current consumption product TC75S102F



TC75S67TU

Noise Characteristic (Toshiba internal comparison)

Reduce 1/f noise (10 Hz) by 86 % from our normal products



[Note] Sensor types: vibration, shock, acceleration, pressure, infrared, temperature, etc.

Lineup		
Part number	TC75S102F	TC75S67TU
Package	SMV	UFV
V _{DD} - V _{SS} [V]	1.5 to 5.5	2.2 to 5.5
V _{IO} (Max) [mV]	1.3	3
CMV _{IN} (Max) [V]	V_{DD}	1.4 (@V _{DD} = 2.5 V)
I _{DD} (Typ. / Max) [μA]	0.27 / 0.46 (@V _{DD} = 1.5 V)	430 / 700 (@V _{DD} = 2.5 V)
V _{NI} (Typ.) [nV/√Hz] @f = 1 kHz	-	6

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High heat efficiency



Value provided

Built-in 50 % duty control function in UART, compatible with Home Bus System (HBS).

Built-in Arm® Cortex®-M3 CPU core

TMPM381 and TMPM383 implement Cortex -M3 core with 40 MHz maximum operation frequency. Various development tool and their partners allow users many options.

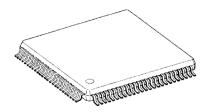
Compatible with HBS

UART function is equipped with 50 % duty control function and is compatible with HBS. A control system composed of HBS can be easily constructed using centralized management systems or thermostats.

Reducing system cost and development load

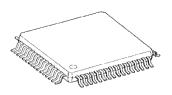
TMPM381 and TMPM383 execute system monitoring efficiently by using built-in AD converter. The original NANOFLASHTM is possible to rewrite at high speed. It reduces user software development time period.

TMPM381FWFG



LOFP100

TMPM383FSUG



LQFP64

Lineup

Part number	TMPM381FWFG	TMPM383FSUG	
Maximum operation frequency	40 MHz	40 MHz	
Instruction ROM	128 KB	64 KB	
RAM	10 KB	8 KB	
Timer	16bit x 8ch	16bit x 8ch	
UART / SIO	3ch	2ch	
UART (50% duty)	1ch	1ch	
AD Converter	18ch (12bit)	10ch (12bit)	

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